

**AMENDMENTS TO THE CLAIMS:**

Please replace the claims with the claims provided in the listing below wherein status, amendments, additions and cancellations are indicated.

1. (Currently amended) A dry etching process including:
  - providing a substrate having a plurality of stacked layers including metal layers a base of glass;
  - introducing a processing gas into a vacuum chamber to achieve a predetermined controlled pressure level therein, the processing gas being one of Cl<sub>2</sub>, and a gaseous mixture containing Cl<sub>2</sub>, CHF<sub>3</sub>, being substantially absent from said processing gas;
  - applying radio frequency power to a substrate placed within the vacuum chamber for generating plasma in the vacuum chamber, whereby the substrate is processed;
  - etching the layers on the substrate with the processing gas until a time point when the surface of a lowermost layer on the substrate is etched; and
  - adding CHF<sub>3</sub> gas to the processing gas for etching the lowermost layer on the substrate, wherein the processing gas is one of Cl<sub>2</sub>, and a gaseous mixture containing Cl<sub>2</sub>, and wherein CHF<sub>3</sub> is substantially absent from said processing gas prior to said step of adding CHF<sub>3</sub>,

2. (Original) The dry etching process according to Claim 1, wherein the etching process is effected through a method of determining a layer being processed.

3. (Original) The dry etching process according to Claim 1, wherein the lowermost layer on the substrate is the subject to be etched.

4. (Original) The dry etching process according to claim 2, wherein the method of determining is monitoring the etching process by detecting plasma light intensity.

5. (Canceled)

6. (Previously presented) The dry etching process according to Claim 4, wherein a non-aluminum reactive gas is added when the substrate includes a layer of aluminum.

7. (Original) The dry etching process according to Claim 6, wherein the proportion of CHF<sub>3</sub> gas is 40% or less with respect to the total flow rate of the processing gas.

8. (Original) The dry etching process according to Claim 6, wherein the proportion of CHF<sub>3</sub> gas is between 5% and 40% with respect to the total flow rate of the processing gas.

9. (Original) The dry etching process according to Claim 6, wherein the proportion of CHF<sub>3</sub> gas is 15% or less with respect to the total flow rate of the processing gas.

10. (Original) The dry etching process according to Claim 6, wherein the proportion of CHF<sub>3</sub> gas is between 5% to 15% with respect to the total flow rate of the processing gas.

11. (Original) The dry etching process according to Claim 6, wherein the proportion of CHF<sub>3</sub> gas is between 15% to 40% with respect to the total flow rate of the processing gas.

12. (Original) The dry etching process according to one of Claims 7-11, wherein the lowermost layer on the substrate includes titanium.

13. (Original) The dry etching process according to one of Claims 7-11, wherein the metal layers of the plurality of stacked layers comprise an aluminum middle layer and titanium top and bottom layers.

14. (Original) The dry etching process according to Claim 2, wherein the method of determining is based upon the sampling data obtained from the experimentation.

15. (Canceled)

16. (Previously Presented) The dry etching process according to Claim 14, wherein a non-aluminum reactive gas is added when the substrate includes a layer of aluminum.

17. (Original) The dry etching process according to Claim 16, wherein the proportion of CHF<sub>3</sub> gas is 40% or less with respect to the total flow rate of the processing gas.

18. (Original) The dry etching process according to Claim 16, wherein the proportion of CHF<sub>3</sub> gas is between 5% and 40% with respect to the total flow rate of the processing gas.

19. (Original) The dry etching process according to Claim 16, wherein the proportion of CHF<sub>3</sub> gas is 15% or less with respect to the total flow rate of the processing gas.

20. (Original) The dry etching process according to Claim 16, wherein the proportion of CHF<sub>3</sub> gas is between 5% and 15% with respect to the total flow rate of the processing gas.

21. (Original) The dry etching process according to Claim 16, wherein the proportion of CHF<sub>3</sub> gas is between 15% and 40% with respect to the total flow rate of the processing gas.

22. (Original) The dry etching process according to one of Claims 17-21, wherein the lowermost layer on the substrate includes titanium.

23. (Original) The dry etching process according to one of Claims 17-21, wherein the metal layers of the plurality of stacked layers comprise an aluminum middle layer and titanium top and bottom layers.